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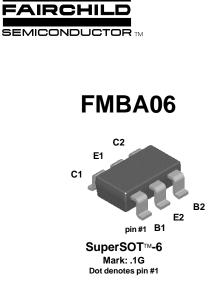


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FMBA06



NPN Multi-Chip General Purpose Amplifier

This device is designed for general purpose amplifier applications at collector currents to 300 mA. Sourced from Process 33.

Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	80	V
V _{CBO}	Collector-Base Voltage	80	V
V _{EBO}	Emitter-Base Voltage	4.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristic

$T_A = 25^{\circ}C$ unless otherwise	se noted
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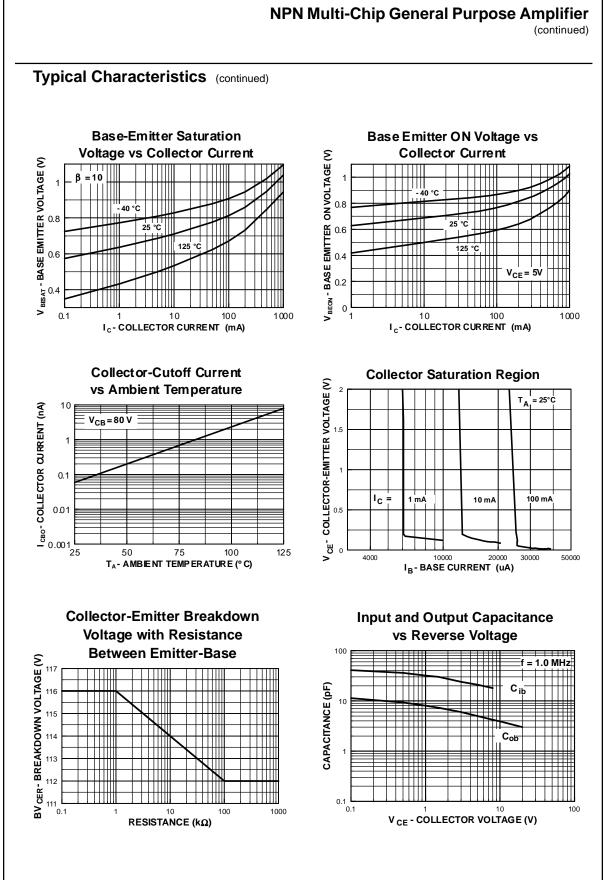
Symbol	Characteristic	Мах	Units
		FMBA06	
PD	Total Device Dissipation	700	mW
	Derate above 25°C	5.6	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	°C/W

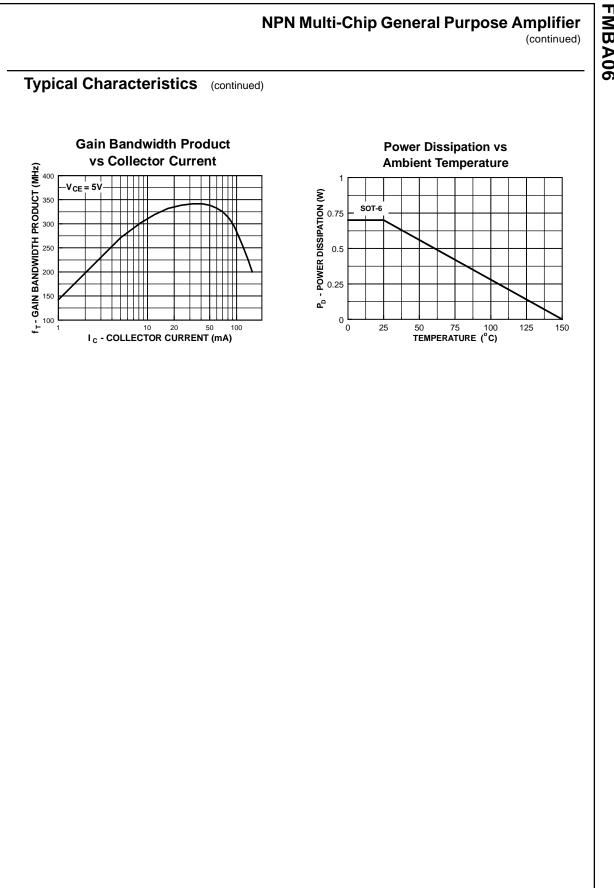
NPN Multi-Chip General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
	RACTERISTICS		00			
/ _{(BR)CEO}	Collector-Emitter Sustaining Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	80			V
(BR)EBO	Emitter-Base Breakdown Voltage	$I_E = 100 \ \mu A, I_C = 0$	4.0		<u> </u>	V
CEO	Collector-Cutoff Current	$V_{CE} = 60 \text{ V}, I_B = 0$			0.1	μA
СВО	Collector-Cutoff Current	$V_{CB} = 80 \text{ V}, I_E = 0$			0.1	μA
ON CHAR	ACTERISTICS					
IFE	DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100 100			
CE(sat)	Collector-Emitter Saturation Voltage	$I_{C} = 100 \text{ mA}, V_{CE} = 1.0 \text{ V}$ $I_{C} = 100 \text{ mA}, I_{B} = 10 \text{ mA}$	100		0.25	V
BE(on)	Base-Emitter On Voltage	$I_{\rm C} = 100 \text{ mA}, V_{\rm CE} = 1.0 \text{ V}$			1.2	V
MALL SI	GNAL CHARACTERISTICS	$I_{C} = 10 \text{ mA}, V_{CE} = 2.0 \text{ V},$		100	1	MHz
1	Current Gain - Danowidth Troduct	f = 100 MHz		100		
Spice	Pulse Width ≤ 300 µs, Duty Cycle ≤ 2.0% Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F					
Spice NPN (Is= Ikr=0 Rc: Vtf=4 Xtf	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F f=6 Rb=10)					
Spice NPN (Is= Ikr=0 Rc: Vtf=4 Xtf	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F					
Spice NPN (Is= Ikr=0 Rc: Vtf=4 Xtt	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F f=6 Rb=10) al Characteristics Typical Pulsed Current Gain	c=.5 Cje=55.61p Mje=.3834 Vje	e=.75 Tr=7	^{2.15n T}	f=516.1p	
Spice NPN (Is= Ikr=0 Rca Vtf=4 Xtt	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F f=6 Rb=10) al Characteristics	c=.5 Cje=55.61p Mje=.3834 Vje	e=.75 Tr=7	^{2.15n T}	f=516.1p	
Spice NPN (Is= Ikr=0 Rca Vtf=4 Xtt	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F f=6 Rb=10) al Characteristics Typical Pulsed Current Gain vs Collector Current	c=.5 Cje=55.61p Mje=.3834 Vje	e=.75 Tr=7	^{2.15n T}	f=516.1p	
Spice NPN (Is= Ikr=0 Rca Vtf=4 Xtt	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F f=6 Rb=10) al Characteristics Typical Pulsed Current Gain vs Collector Current	c=.5 Cje=55.61p Mje=.3834 Vje	e=.75 Tr=7	^{2.15n T}	f=516.1p	
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Spice NPN (Is= Ikr=0 Rc: Vtf=4 Xtt	Model 8.324f Xti=3 Eg=1.11 Vaf=100 Bf=12.1 =.25 Cjc=18.36p Mjc=.3843 Vjc=.75 F f=6 Rb=10) al Characteristics Typical Pulsed Current Gain vs Collector Current 125 °C 25 °C	c=.5 Cje=55.61p Mje=.3834 Vje Collector Voltage v $\beta = 10$ $\beta = 10$ β	e=.75 Tr=7	Satur tor Cu	ation Irrent 125 °C °C -40 °C 100	0 Itf=.5

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